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**(54) Title (EN):** CONFINED AND SCALABLE HELMET

**(54) Title (FR):** CASQUE CONFINÉ ET EXTENSIBLE

**(57) Abstract:**

**(EN):** An embodiment includes a system comprising: a first gate and a first contact that correspond to a transistor and are on a first fin; a second gate and a second contact that correspond to a transistor and are on a second fin; an interlayer dielectric (ILD) collinear with and between the first and second contacts; wherein (a) the first and second gates are collinear and the first and second contacts are collinear; (b) the ILD includes a recess that comprises a cap layer including at least one of an oxide and a nitride. Other embodiments are described herein.

**(FR):** Selon un mode de réalisation, l'invention concerne un système comprenant : une première grille et un premier contact qui correspondent à un transistor et sont situés sur une première ailette ; une seconde grille et un second contact qui correspondent à un transistor et se trouvent sur une seconde ailette ; et un diélectrique intercouche (ILD) colinéaire avec les premier et second contacts et situé entre ces derniers ; dans lequel (a) les première et seconde grilles sont colinéaires et les premier et second contacts sont colinéaires ; et (b) l'ILD comporte un évidement qui comprend une couche de recouvrement comprenant un oxyde et/ou un nitrure. D'autres modes de réalisation sont décrits dans la description.

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**Declarations:**

Declaration made as to the identity of the inventor (PCT Rules 4.17(i) and 51bis.1(a)(i))

Declaration made as applicant's entitlement, as at the international filing date, to apply for and be granted a patent (Rules 4.17(ii) and 51bis.1(a)(ii)), in a case where the declaration under Rule 4.17(iv) is not appropriate